

ABSTRACT

A single-crystal silicon carbide wafer of the present invention includes boron at a concentration of 1.0×10^{16} atoms/cm³ or less, and a region where a misorientation in a crystal
5 plane of the single-crystal silicon carbide wafer (31) is 50 arcsec or less is present on the surface. An area of the region is one fourth or more of an area of the surface of the single-crystal silicon carbide wafer.

FIG. 1